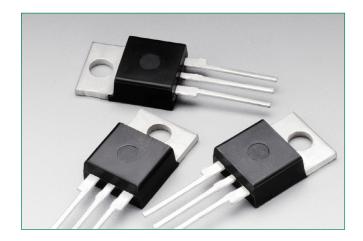
MAC8DG, MAC8MG, MAC8NG

Surface Mount - 400V -800V







Description

Designed for high performance full—wave ac control applications where high noise immunity and high commutating di/dt are required. The MAC8xG series is designed for high performance full-wave AC control applications where high noise immunity and high commutating di/dt are required.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 8.0 Amperes RMS at 100°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dv/dt 250 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220 Package
- High Commutating di/dt 6.5 A/ms minimum at 125°C
- These Devices are Pb-Free and are RoHS Compliant

Additional Information







Accessories

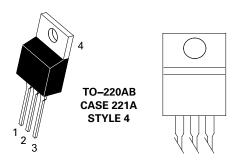


Samples

Functional Diagram



Pin Out





MAC8DG, MAC8MG, MAC8NG Surface Mount – 400V -800V

Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = -40^{\circ}$ to 125°C)	MAC8DG MAC8MG MAC8NG	V _{DRM} , V _{RRM}	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_{\rm c}$ = 10	00°C)	I _{T (RMS)}	8.0	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _c = 125°C)	I _{TSM}	80	А	
Circuit Fusing Consideration (t = 8.3 ms)	l²t	26	A ² sec	
Peak Gate Power (Pulse Width \leq 1.0 μ s, $T_{\rm C}$ = 80°C)	P _{GM}	16	W	
Average Gate Power (t=8.3ms, $T_J = 80^{\circ}$ C)		P _{G(AV)}	0.35	W
Operating Junction Temperature Range		T _J	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

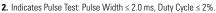
Rating		Symbol	Value	Unit
Thermal Resistance,	Junction—to—Case (AC) Junction—to—Ambient	R _{ejc} R _{eja}	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purpose	s, 1/8" from case for 10 seconds	T_L	260	°C

Electrical Characteristics - OFF ($TJ = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T ₁ = 25°C	I _{DRM} ,	-	-	0.01	mΛ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	T _J = 125°C	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - ON ($TJ = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On–State Voltage (Note 4) ($I_{TM} = \pm 6.0 \text{ A}$)		V_{TM}	_	1.3	1.6	V
Gate Trigger Current	MT2(+), G(+)		5.0	13	35.0	
(Continuous dc)	MT2(+), G(-)	I _{GT}	5.0	16	35.0	mA
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)		5.0	18	35.0	
Holding Current ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = $\pm 150 \text{ mA}$))	l _H	_	20	40	mA
1	MT2(+), G(+)		_	20	50	mA
Latching Current $(V_D = 24 \text{ V, } I_C = 35 \text{ mA})$	MT2(+), G(-)	I _L	_	30	80	
(* _D = 2 : *, 1 _G = 33 : : : : : : : : : : : : : : : : :	MT2(-), G(-)		_	20	50	
0 . T	MT2(+), G(+)	$V_{\rm GT}$	0.5	0.69	1.5	V
Gate Trigger Voltage $(V_D = 12 \text{ V, R}_1 = 100 \Omega)$	MT2(+), G(-)		0.5	0.77	1.5	
$(V_D - 12, V, 11_L - 100, 22)$	MT2(-), G(-)		0.5	0.72	1.5	
Gate Non-Trigger Voltage	MT2(+), G(+)		0.2	-	-	
$(T_{J} = 125^{\circ}C)$	MT2(+), G(-)	V_{GD}	0.2	_	-	V
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)		0.2	-	-	





^{1.} V_{DBM} and V_{SBM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

MAC8DG, MAC8MG, MAC8NG Surface Mount – 400V -800V

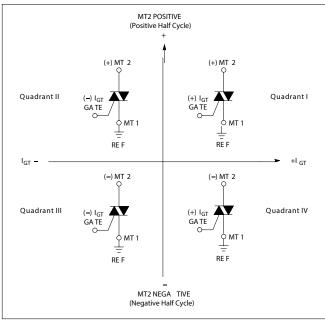
Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current See Figure 10.($V_D = 400 \text{ V}$, $I_{TM} = 4.4 \text{ A}$, Commutating dv/dt = 18 V/ μ s, Gate Open, $T_J = 125^{\circ}\text{C}$, $f = 250 \text{ Hz}$, No Snubber) $C_I = 10 \ \mu\text{F}$ $L_I = 40 \text{ mH}$	(dv/dt)c	6.5	-	-	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)$	dV/dt	250	-	_	V/µs

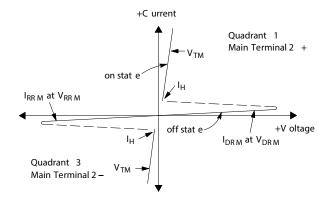
Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in–phase signals (using standard AC lines) quadrants I and III are used





MAC8DG, MAC8MG, MAC8NG Surface Mount – 400V -800V

Figure 1. RMS Current Derating

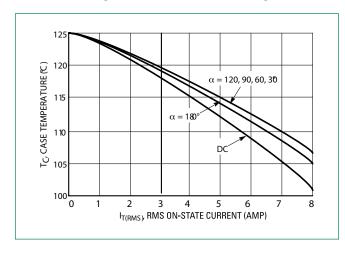


Figure 3. On-State Characteristics

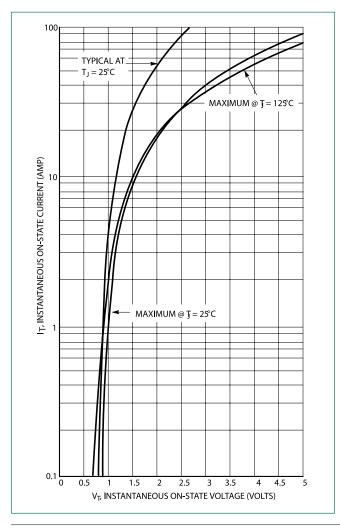


Figure 2. On-State Power Dissipation

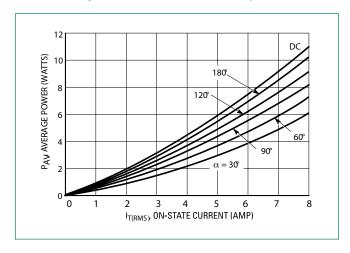


Figure 4. Thermal Response

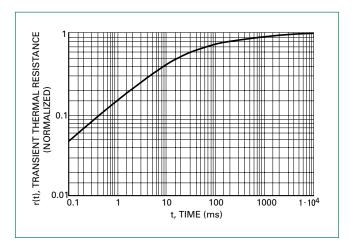
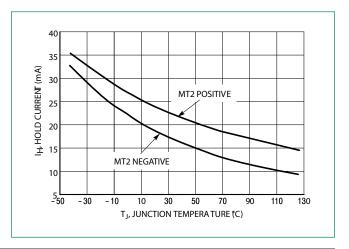


Figure 5. Hold Current Variation





MAC8DG, MAC8MG, MAC8NG

Surface Mount - 400V -800V

Figure 6. Gate Trigger Current Variation

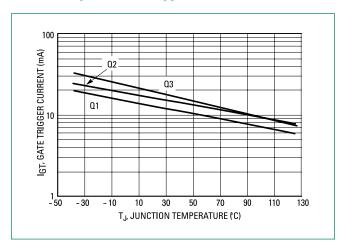


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential)

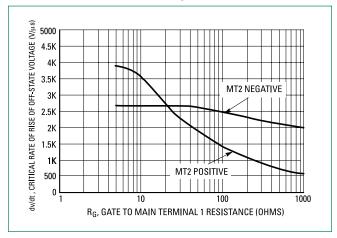


Figure 7. Gate Trigger Voltage Variation

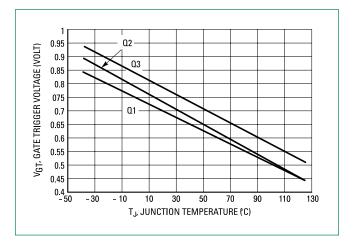


Figure 9. Critical Rate of Rise of Commutating Voltage

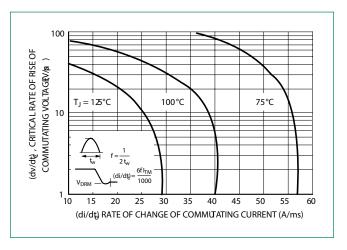
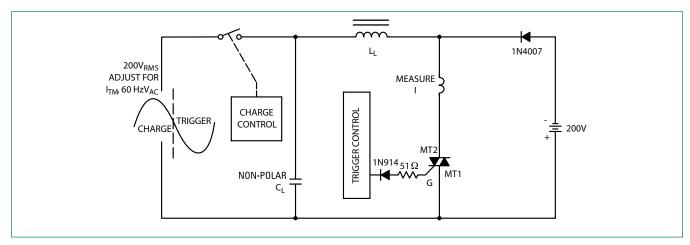


Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)



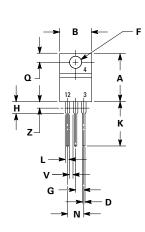
Note: Component values are for verification of rated (di/dt)_c. See AN1048 for additional information

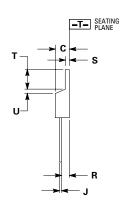


MAC8DG, MAC8MG, MAC8NG

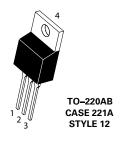
Surface Mount - 400V -800V

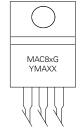
Dimensions





Part Marking System





x =D, M, or N Y =Year

M =Month A =Assembly Site

XX =Lot Serial Code

G =Pb-Free Package

Dim	Inches		Millin	neters
DIM	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	No Connection			

Ordering Information

Device	Package	Shipping	
MAC8DG			
MAC8MG	TO-220AB (Pb-Free)	1000 Units / Box	
MAC8NG	(151100)		

2. Controlling dimension: inch.



^{1.} Dimensioning and tolerancing per ansi y14.5m, 1982.

^{3.} Dimension z defines a zone where all body and lead irregularities are allowed.

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BTB16Q-600BW Z0409MF BTA04-600B BTA06-600BRG BTA06-800BWRG BTA08-600BRG BTA08-800B BT136-600,127

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